



# 1-Line Bi-directional TVS Diode

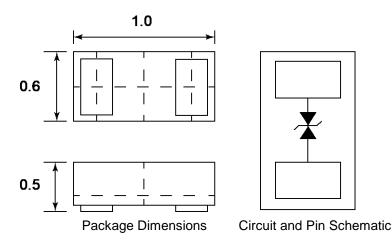
### **Description**

The PESDU2421P1 is a bi-directional TVS diode, it is designed to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU2421P1 complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±20kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD protection make PESDU2421P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

#### **Features**

- Ultra small package: 1.0x0.6x0.5mm
- Protects one data or power line
- Operating voltage: 24V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±25kV
    - Contact discharge: ±20kV
  - IEC61000-4-5 (Lightning) 3A (8/20µs)
- RoHS Compliant

### **Dimensions and Pin Configuration**



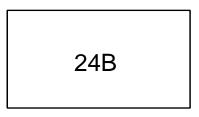
#### **Mechanical Characteristics**

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

### **Applications**

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players

### Marking Information



24B = Device Marking Code

### **Ordering Information**

Part Number	Shiping	Reel Size
PESDU2421P1	10000/Tape & Reel	7 inch



# Absolute Maximum Ratings (TA=25°C unless otherwise specified)

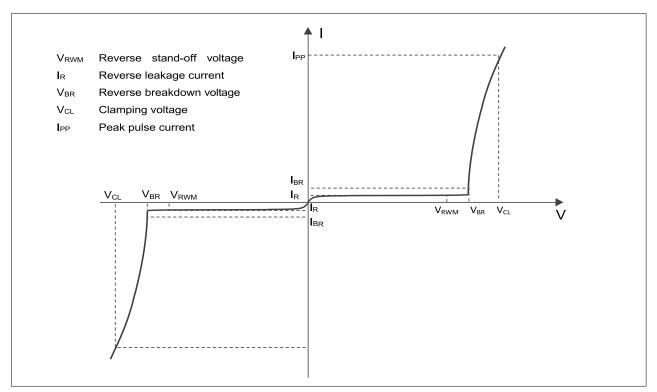
Parameter	Symbol	Value	Unit		
Peak Pulse Power (8/20µs)	Ррк	180	W		
Peak Pulse Current (8/20µs)	Ірр	3	А		
ESD per IEC 61000-4-2 (Air)	Mara	±25			
ESD per IEC 61000-4-2 (Contact)	Vesd	±20	kV		
Lead temperature	TL	260	°C		
Operating Temperature Range	Тор	-40 ~ +85	°C		
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +150	°C		

# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	V <sub>BR</sub>	27			V	I <sub>T</sub> = 1mA
Reverse Leakage Current	IR			0.2	μA	$V_{RWM} = 24V$
Clamping Voltage	Vc			60	V	I <sub>PP</sub> = 3A (8/20µs pulse),
Junction Capacitance	CJ		10		pF	$V_R = 0V, f = 1MHz$



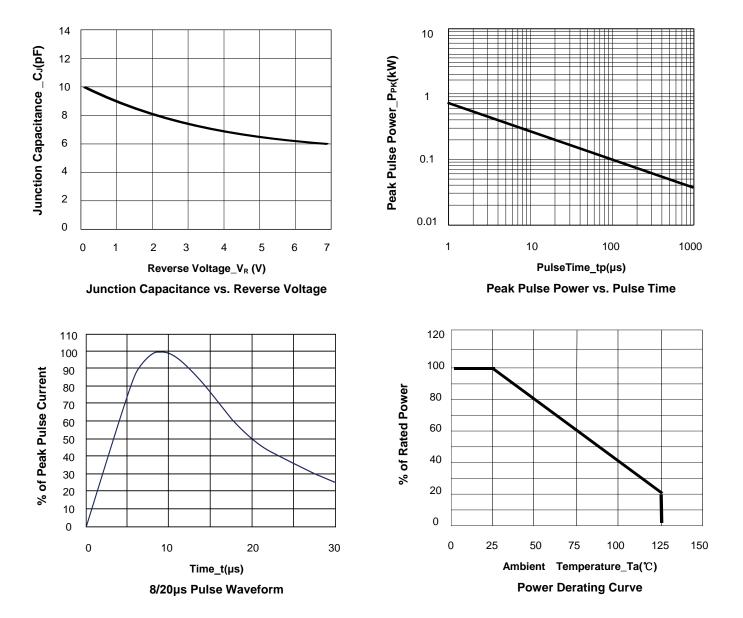
# Electrical characteristics ( $T_A = 25^{\circ}C$ , unless otherwise noted)



### Definitions of electrical characteristics



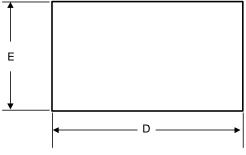
# Typical Performance Characteristics (T<sub>A</sub>=25°C unless otherwise Specified)



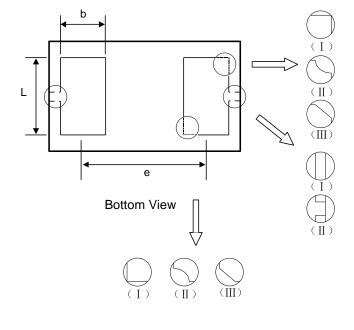


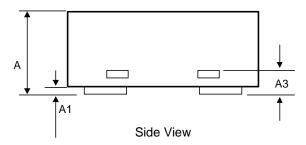


### DFN1006-2 Package Outline Drawing



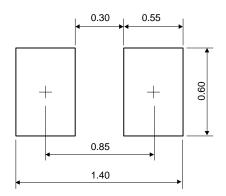
Top View





Symbol	Dimensions in Millimeters			
	Min.	Тур.	Max.	
А	0.340	0.450	0.550	
A1	0.000	0.020	0.050	
A3	0.125 Ref.			
D	0.950	1.000	1.075	
E	0.490	0.600	0.675	
b	0.200	0.250	0.300	
L	0.450	0.500	0.550	
е	0.650 BSC			

# Recommended PCB Layout (Unit: mm)



#### Notes:

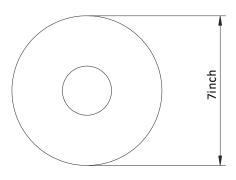
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.



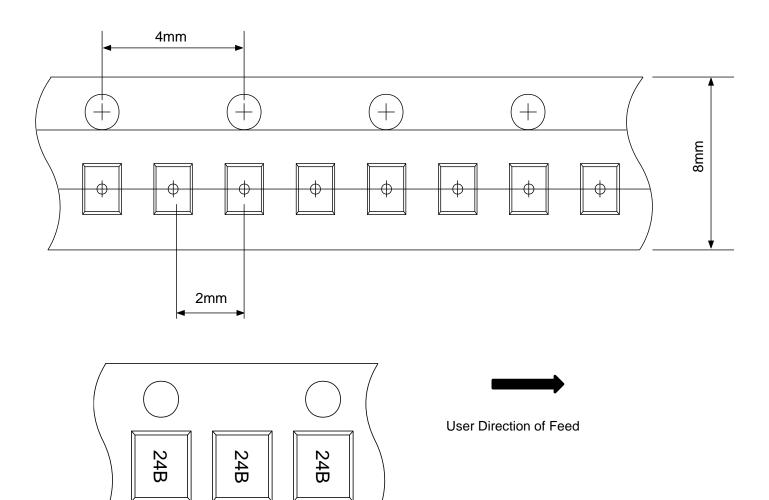


# TAPE AND REEL INFORMATION

#### **Reel Dimensions**



**Tape Dimensions** 





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